



**THE DATASHEET OF**  
**SI4336DY-T1-E3**



## N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	r <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ)
30	0.00325 at V <sub>GS</sub> = 10 V	25	36
	0.0042 at V <sub>GS</sub> = 4.5 V	22	

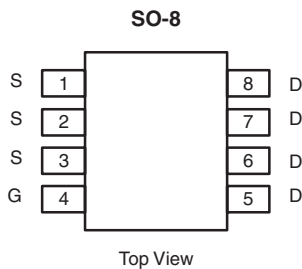
### FEATURES

- Ultra Low On-Resistance Using High Density TrenchFET<sup>®</sup> Gen II Power MOSFET Technology
- Q<sub>g</sub> Optimized
- 100 % R<sub>g</sub> Tested



### APPLICATIONS

- Synchronous Buck Low-Side
  - Notebook
  - Server
  - Workstation
- Synchronous Rectifier, POL



Ordering Information: Si4336DY-T1  
Si4336DY-T1-E3 (Lead (Pb)-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted					
Parameter	Symbol	10 sec	Steady State	Unit	
Drain-Source Voltage	V <sub>DS</sub>	30		V	
Gate-Source Voltage	V <sub>GS</sub>	± 20			
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	I <sub>D</sub>	T <sub>A</sub> = 25 °C	25	17	A
		T <sub>A</sub> = 70 °C	20	13	
Pulsed Drain Current (10 μs Pulse Width)	I <sub>DM</sub>	70			
Continuous Source Current (Diode Conduction) <sup>a</sup>	I <sub>S</sub>	2.9	1.3		
Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	50		
Maximum Power Dissipation <sup>a</sup>	P <sub>D</sub>	T <sub>A</sub> = 25 °C	3.5	1.6	W
		T <sub>A</sub> = 70 °C	2.2	1	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a</sup>	t ≤ 10 sec	R <sub>thJA</sub>	29	35	°C/W
	Steady State		67	80	
Maximum Junction-to-Foot (Drain)	Steady State	R <sub>thJF</sub>	13	16	

Notes:

a. Surface Mounted on 1" x 1" FR4 Board.

\* Pb containing terminations are not RoHS compliant, exemptions may apply.



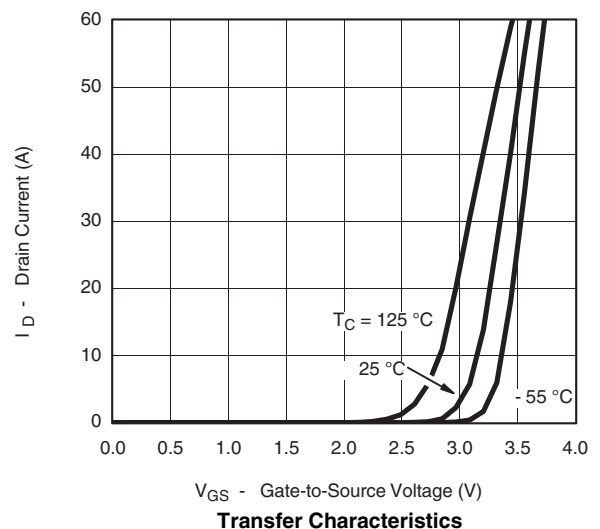
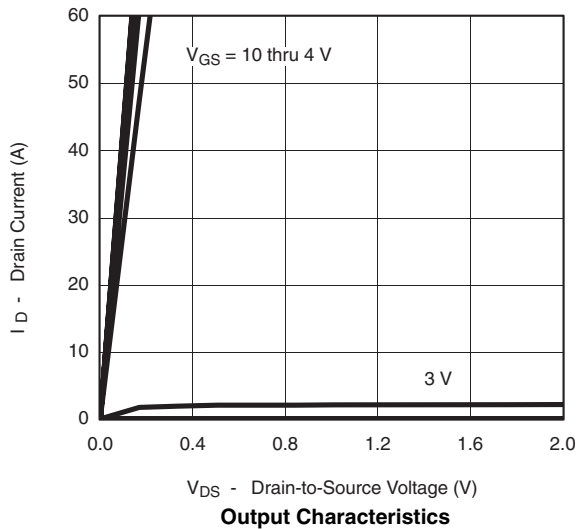
<b>SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>Static</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1.0		3.0	V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			5	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	30			A
Drain-Source On-State Resistance <sup>a</sup>	$r_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 25\text{ A}$		0.0026	0.00325	$\Omega$
		$V_{GS} = 4.5\text{ V}, I_D = 22\text{ A}$		0.0033	0.0042	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 25\text{ A}$		110		S
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = 2.9\text{ A}, V_{GS} = 0\text{ V}$		0.72	1.1	V
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		5600		$\mu\text{F}$
Output Capacitance	$C_{oss}$			860		
Reverse Transfer Capacitance	$C_{rss}$			415		
Total Gate Charge	$Q_g$	$V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 20\text{ A}$		36	50	nC
Gate-Source Charge	$Q_{gs}$			18		
Gate-Drain Charge	$Q_{gd}$			10		
Gate Resistance	$R_g$		0.8	1.3	2.0	$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 15\text{ }\Omega$ $I_D \cong 1\text{ A}, V_{GEN} = 10\text{ V}, R_g = 6\text{ }\Omega$		24	35	ns
Rise Time	$t_r$			16	25	
Turn-Off Delay Time	$t_{d(off)}$			90	140	
Fall Time	$t_f$			32	50	
Source-Drain Reverse Recovery Time	$t_{rr}$		$I_F = 2.9\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		45	

Notes:

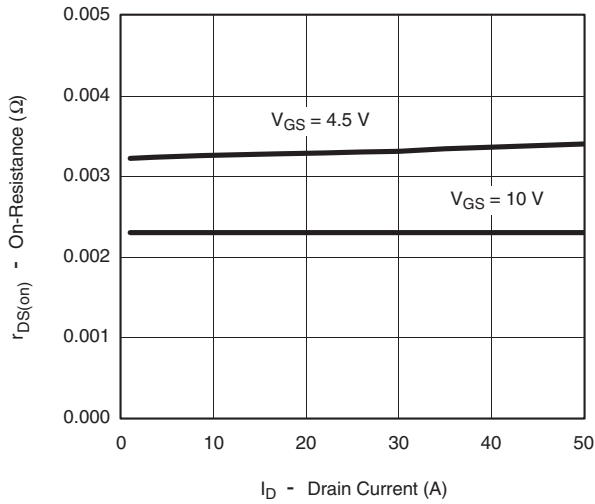
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

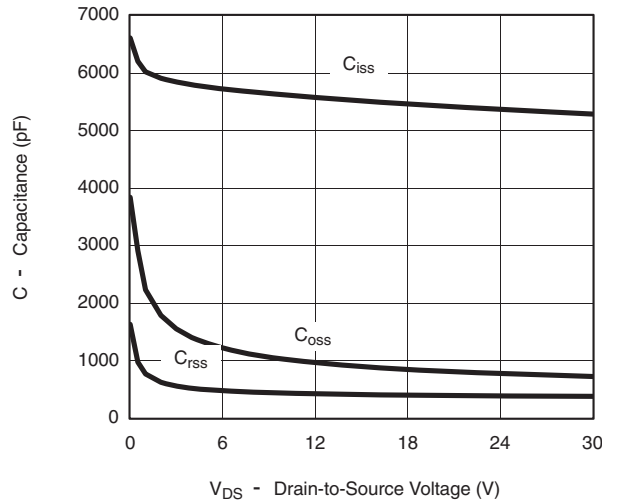
**TYPICAL CHARACTERISTICS**  $25\text{ }^\circ\text{C}$ , unless otherwise noted



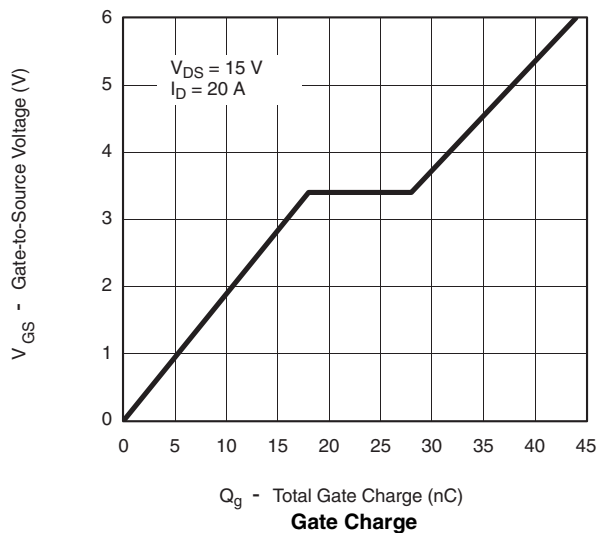
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



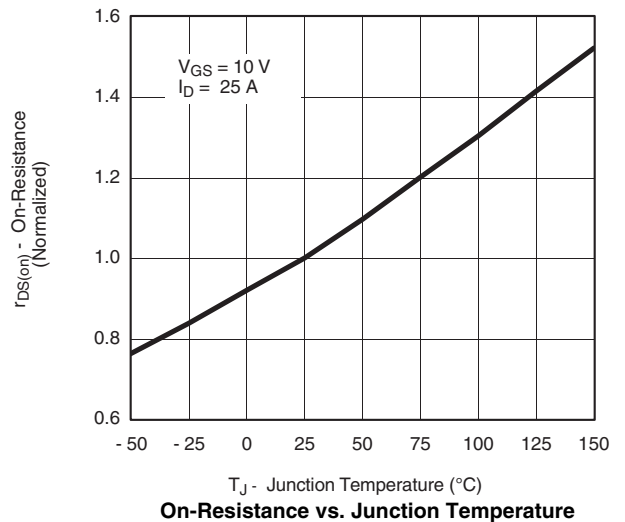
**On-Resistance vs. Drain Current**



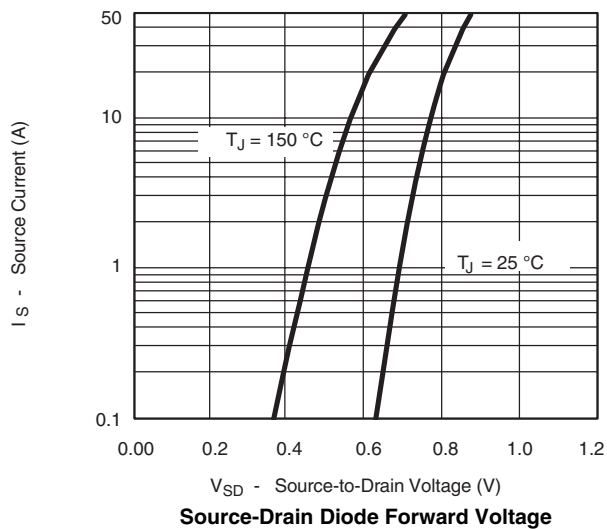
**Capacitance**



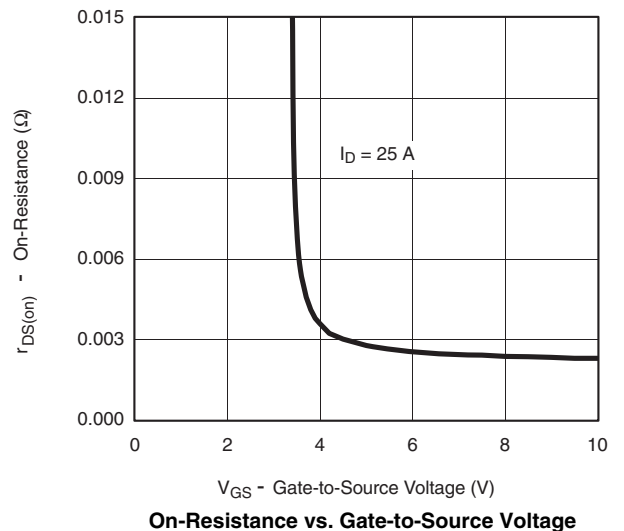
**Gate Charge**



**On-Resistance vs. Junction Temperature**

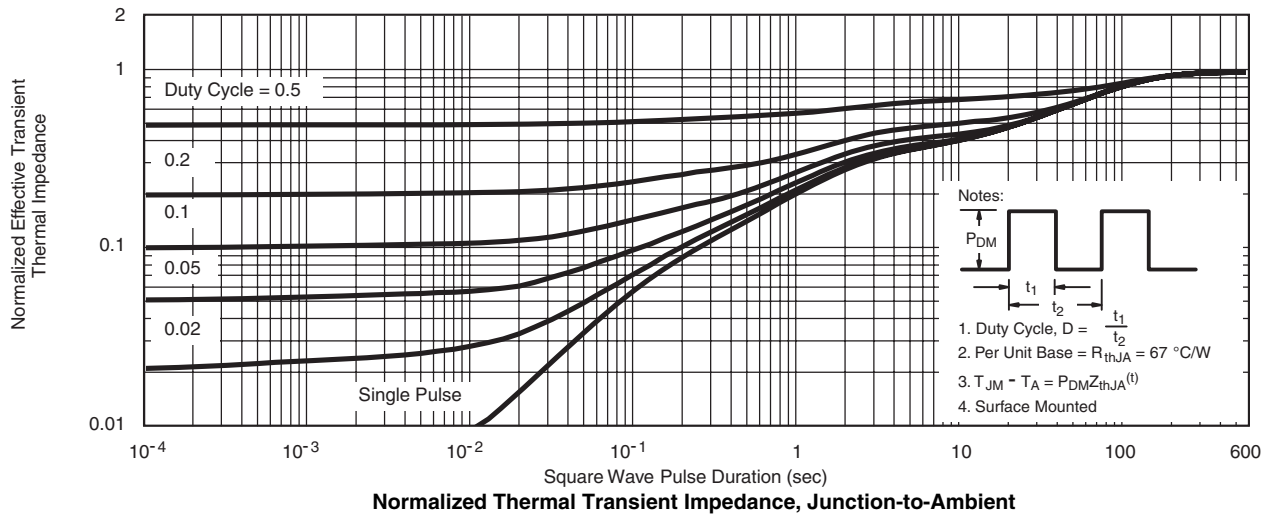
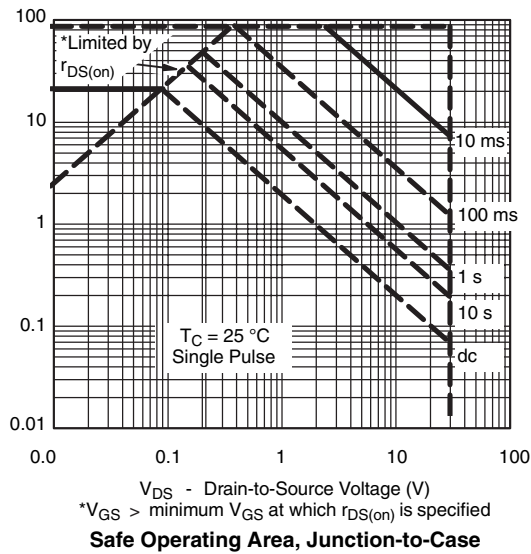
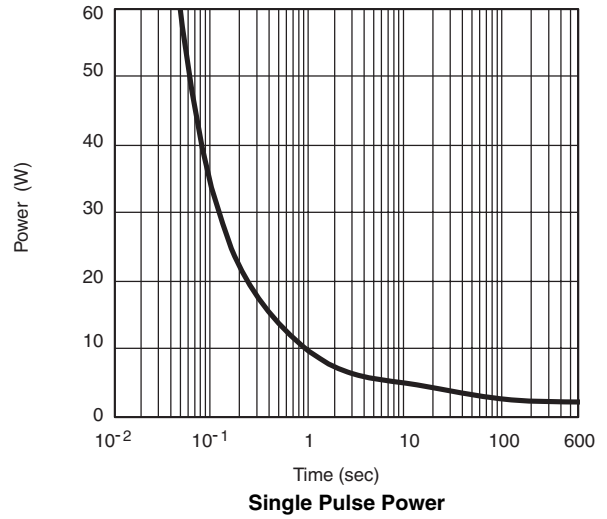
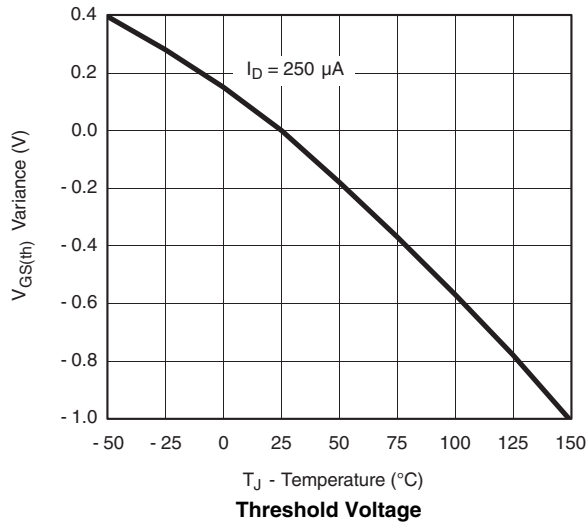


**Source-Drain Diode Forward Voltage**



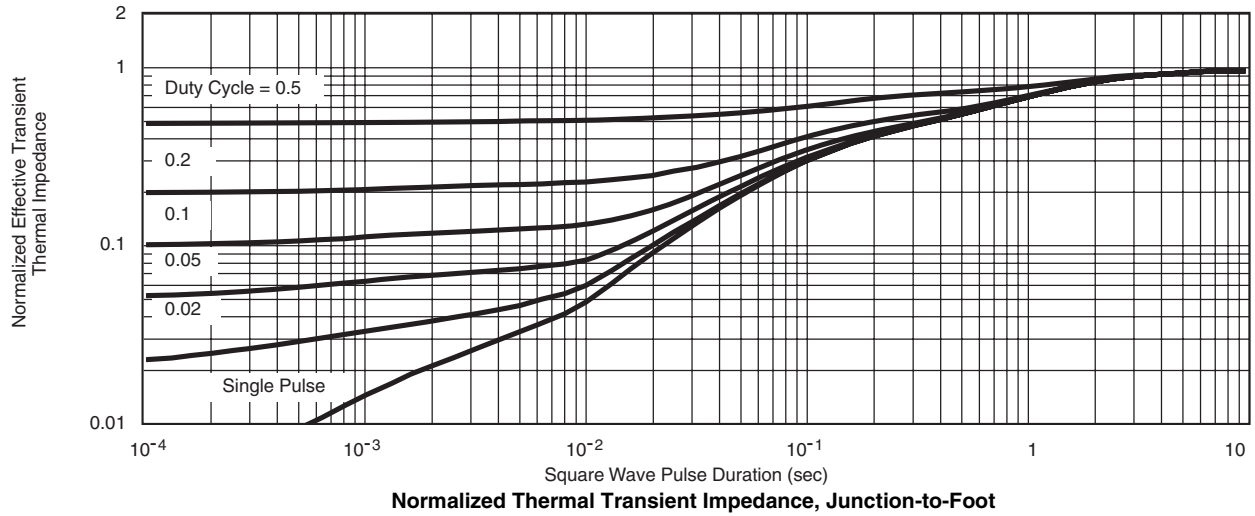
**On-Resistance vs. Gate-to-Source Voltage**

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted





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